SUBSTITUTE FORM PTO-1449 (MODIFIED)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO.: YOR920000693US2	CIP OF SERIAL NO.: 09/748,071
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) (37 CFR 1.98(b))		APPLICANT: Ratnam SOORIYAKUMARAN et al. 10/079,289	
		FILING DATE: Concurrently herewith	GROUP: ~~Unassigned~~ 1752

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	CITE NO.	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SKG	AA	Ser. No. 09/514,212		Brock et al.			2/28/00
	AB	4,189,323	2/19/80	Buhr			
	AC	4,442,197	4/10/84	Crivello et al.			
	AD	4,491,628	1/1/85	Ito et al.			
	AE	4,603,101	7/29/86	Crivello			
	AF	4,624,912	11/25/86	Zweifel et al.			
	AG	4,855,017	8/8/89	Douglas			
	AH	5,338,818	8/16/94	Brunsvold et al.			
	AI	5,344,742	9/6/94	Sinta et al.			
	AJ	5,362,663	11/8/94	Bronner et al.			
	AK	5,385,804	1/31/95	Premlatha et al.			
	AL	5,399,462	3/21/95	Sachdev et al.			
	AM	5,429,710	7/4/95	Akiba et al.			
	AN	5,562,801	10/8/96	Nulty			
	AO	5,580,694	12/3/96	Allen et al.			
	AP	5,618,751	4/8/97	Golden et al.			
CF 3/14/07	AQ	5,679,495	12/21/97	Yamachika et al.			
	AR	5,744,376	4/28/98	Chan et al.			
	AS	5,801,094	9/1/98	Yew et al.			
	AT	5,985,524	11/16/99	Allen et al.			
	AU	6,087,064	7/11/00	Lin et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	CITE NO.	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
	~~AV~~	~~CA 1,204,547~~	~~5/13/86~~	~~Canada~~				
	~~AW~~	~~JP 1-293339~~	~~11/27/89~~	~~Japan~~				

OTHER DOCUMENTS — NONPATENT LITERATURE DOCUMENTS

EXAMINER INITIALS	CITE NO.	INCLUDE NAME OF AUTHOR, TITLE OF ARTICLE (IF APPROPRIATE), TITLE OF PUBLICATION, DATE, PAGE(S), VOLUME-ISSUE NUMBER(S), PUBLISHER, AND PLACE OF PUBLICATION
	AX	Abe et al. (1995), "Study of ArF Resist Material in Terms of Transparency and Dry Etch Resistance," *Journal of Photopolymer Science and Technology*. 8(4):637-642.
	AY	Allen et al. (1995), "Resolution and Etch Resistance of a Family of 193 nm Positive Resists," *Journal of Photopolymer Science and Technology* 8(4):623-636.
	AZ	Allen et al. (1997), "Deep-UV Resist Technology: The Evolution of Materials and Processes for 250-nm Lithography and Beyond," *Handbook of Microlithography, Micromachining, and Microfabrication, Vol. 1: Microlithography*, P. Raj-Coudhury, Ed., p 321-375.
	BA	Baney et al. (1995), "Silsesquioxanes," *Chemical Reviews* 95(5):2409-1430.
	BB	Crawford et al. (2000), "New Materials for 157 nm Photoresists: Characterization and Properties," *Proceedings of SPIE* 3999:357-364.
	BC	Fujigaya et al. (2000), "Chemically Amplified Positive Resist Based on Silsesquioxane for 157nm Lithography," *Extended Abstracts, 12th International Conference on Photopolymers - Principles, Processes, and Materials*, The Legends Resort and Country Club, McAfee, New Jersey, page P39.

EXAMINER SIGNATURE: S. Gillian	DATE CONSIDERED: 12/27/05

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.